

PBSS4160U

60 V, 1 A NPN low V_{CEsat} (BISS) transistor

Rev. 03 — 11 December 2009

Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT323 (SC-70) Surface Mounted Device (SMD) plastic package.

PNP complement: PBSS5160U.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- High voltage DC-to-DC conversion
- High voltage MOSFET gate driving
- High voltage motor control
- High voltage power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1. Quick reference data

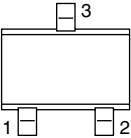
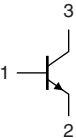
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	60	V
I_C	collector current (DC)		[1]	-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	2	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 1$ A; $I_B = 100$ mA	[2]	-	230	$m\Omega$

[1] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

[2] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	base		 sym021
2	emitter		
3	collector		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4160U	SC-70	plastic surface mounted package; 3 leads	SOT323

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBSS4160U	52*

- [1] * = -: made in Hong Kong
* = p: made in Hong Kong
* = t: made in Malaysia
* = W: made in China

5. Limiting values

Table 5. Limiting values

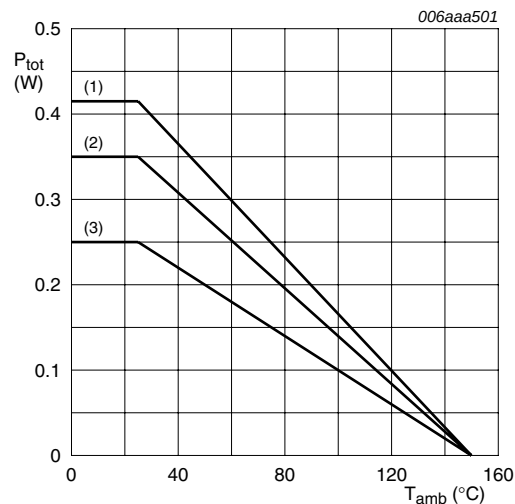
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	80	V
V_{CEO}	collector-emitter voltage	open base	-	60	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I_C	collector current (DC)		[1] -	750	mA
			[2] -	930	mA
			[3] -	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	2	A
I_B	base current (DC)		-	300	mA
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1] -	250	mW
			[2] -	350	mW
			[3] -	415	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

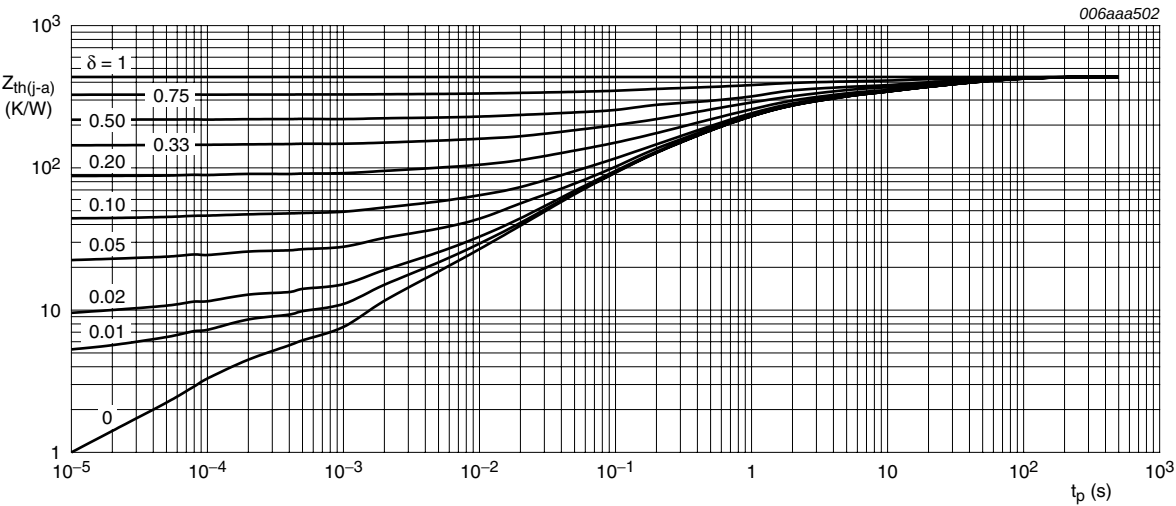
Fig 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

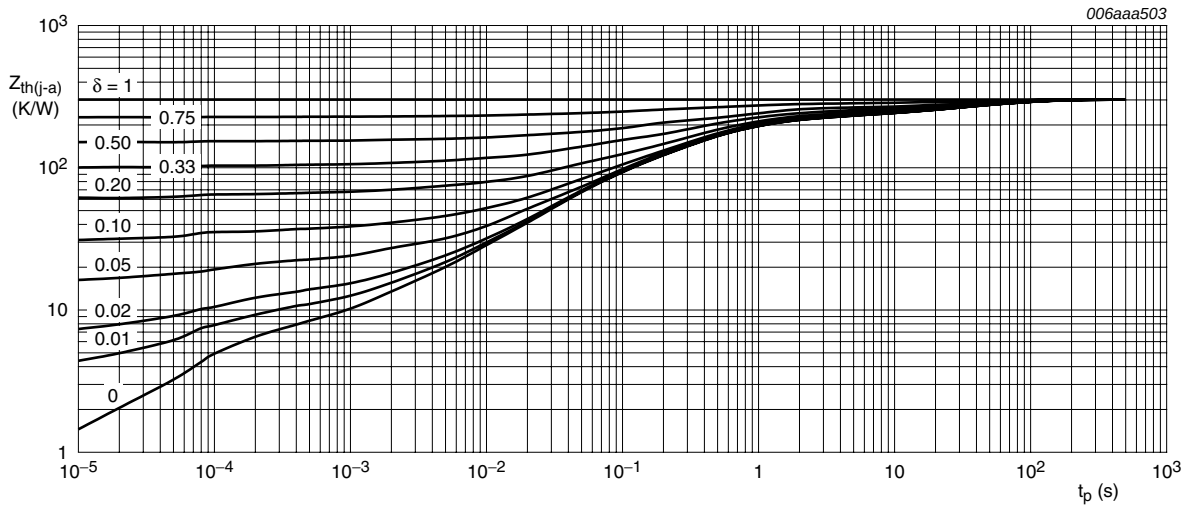
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W
			[2] -	-	357	K/W
			[3] -	-	301	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	150	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



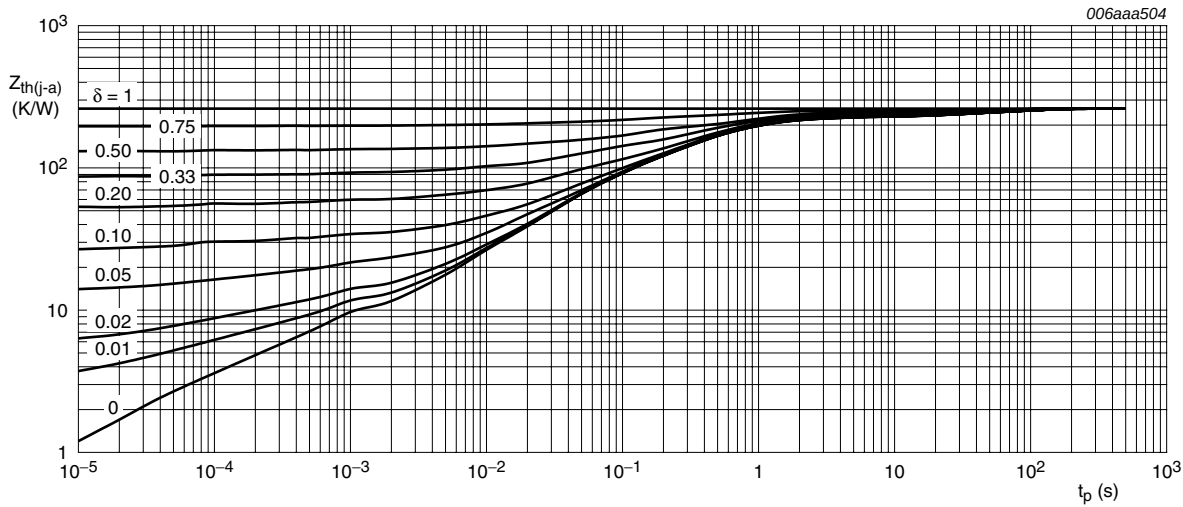
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse time; typical values



FR4 PCB, mounting pad for collector 1 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

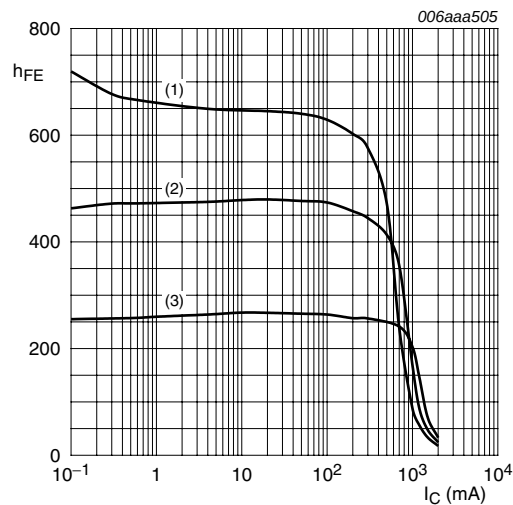
7. Characteristics

Table 7. Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

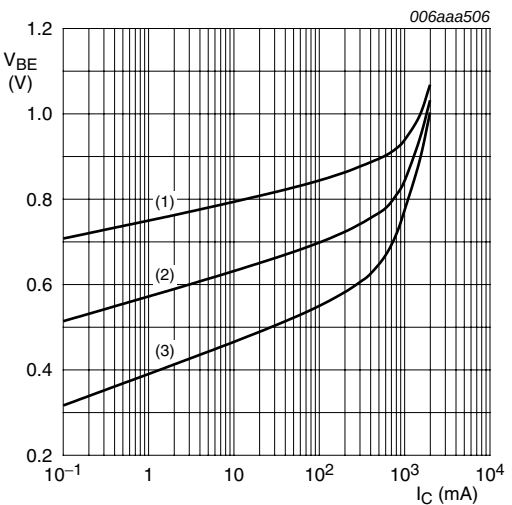
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 60\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
		$V_{CB} = 60\text{ V}; I_E = 0\text{ A}; T_J = 150\text{ }^{\circ}\text{C}$	-	-	50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = 60\text{ V}; V_{BE} = 0\text{ V}$	-	-	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	250	500	-	
		$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$ [1]	200	420	-	
		$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$ [1]	100	180	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	-	90	115	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	-	120	150	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$ [1]	-	230	280	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = 1\text{ A}; I_B = 100\text{ mA}$ [1]	-	230	280	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 50\text{ mA}$ [1]	-	0.95	1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$ [1]	-	0.85	0.9	V
t_d	delay time	$I_C = 0.5\text{ A}; I_{Bon} = 25\text{ mA}; I_{Boff} = -25\text{ mA}$	-	11	-	ns
t_r	rise time		-	78	-	ns
t_{on}	turn-on time		-	90	-	ns
t_s	storage time		-	340	-	ns
t_f	fall time		-	160	-	ns
t_{off}	turn-off time		-	500	-	ns
f_T	transition frequency	$V_{CE} = 10\text{ V}; I_C = 50\text{ mA}; f = 100\text{ MHz}$	150	220	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	5.5	10	pF

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.



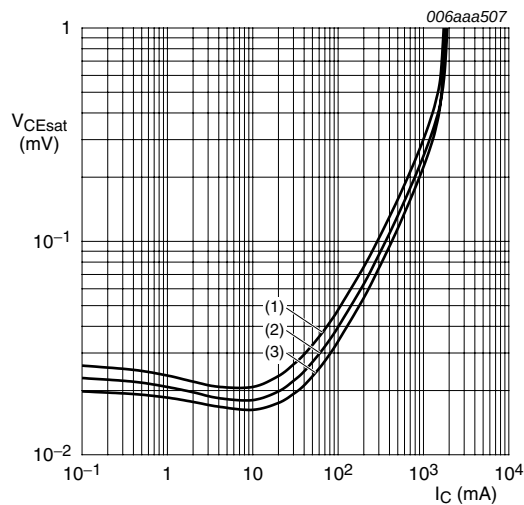
- $V_{CE} = 5\text{ V}$
- (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 5. DC current gain as a function of collector current; typical values



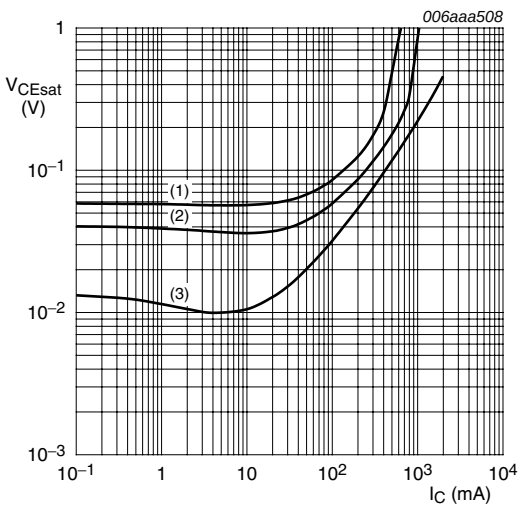
- $V_{CE} = 5\text{ V}$
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 6. Base-emitter voltage as a function of collector current; typical values



- $I_C/I_B = 20$
- (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



- $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (1) $I_C/I_B = 100$
 - (2) $I_C/I_B = 50$
 - (3) $I_C/I_B = 10$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

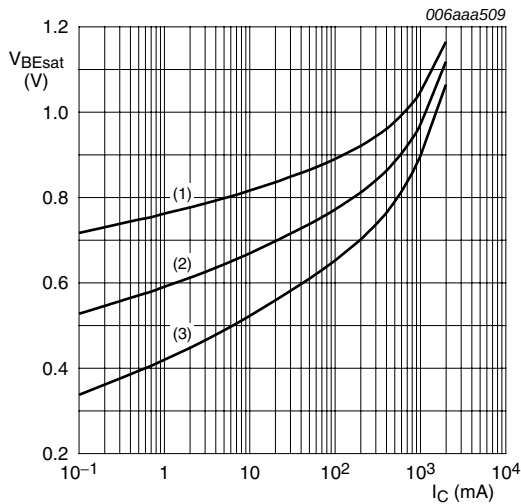


Fig 9. Base-emitter saturation voltage as a function of collector current; typical values

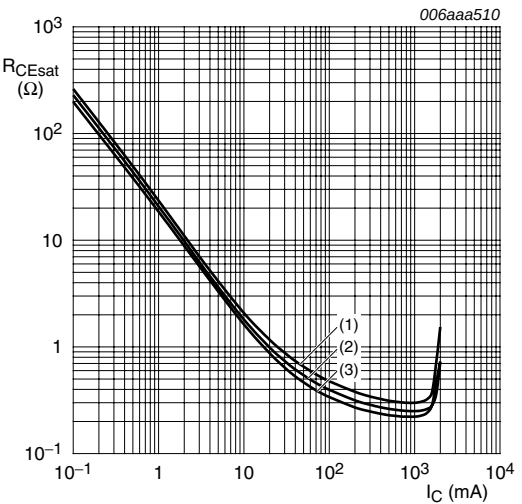


Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

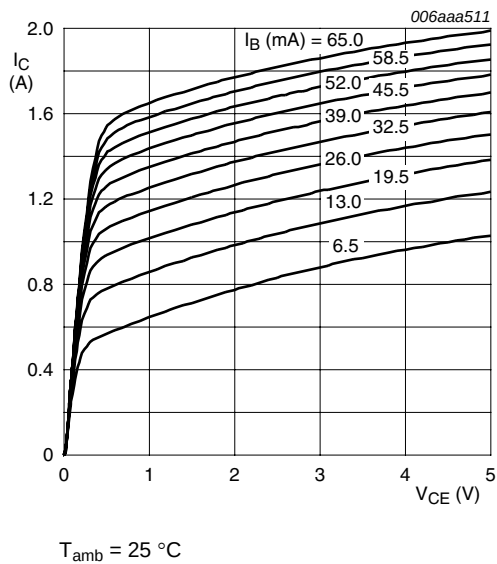


Fig 11. Collector current as a function of collector-emitter voltage; typical values

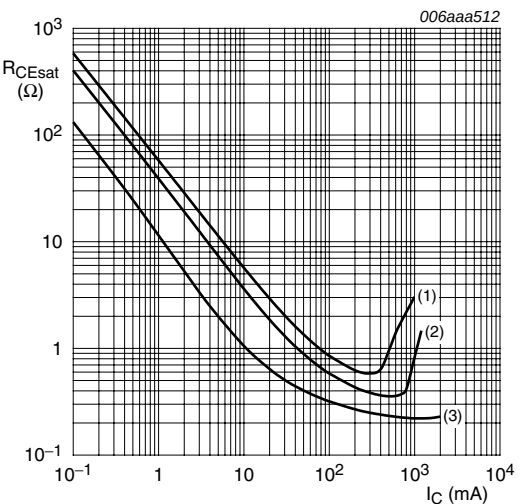


Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

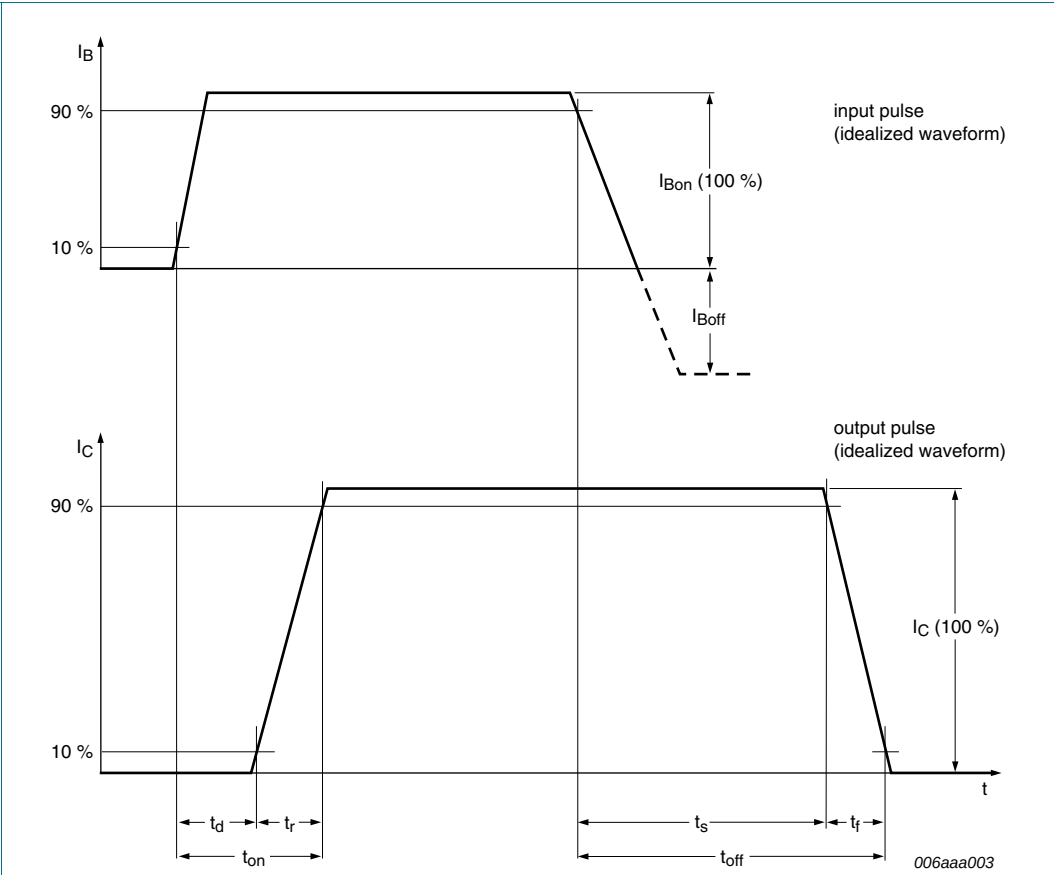


Fig 13. BISS transistor switching time definition

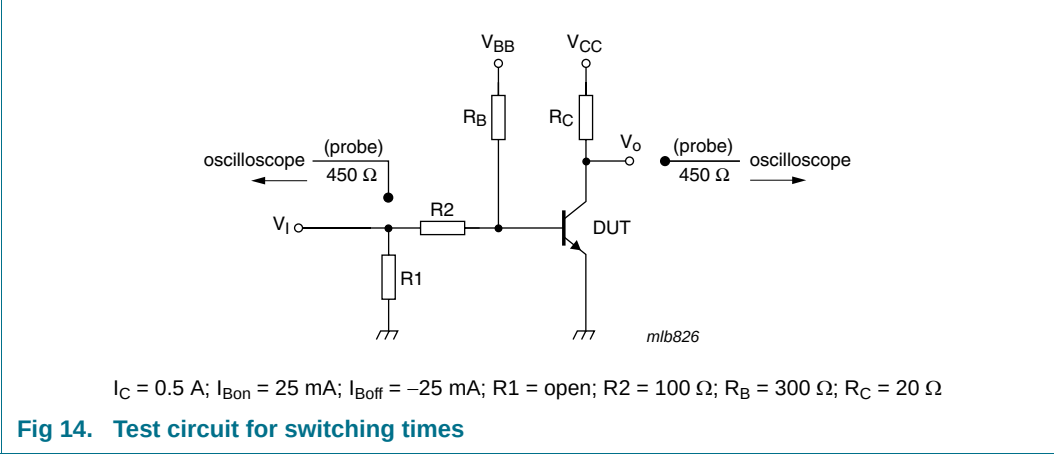
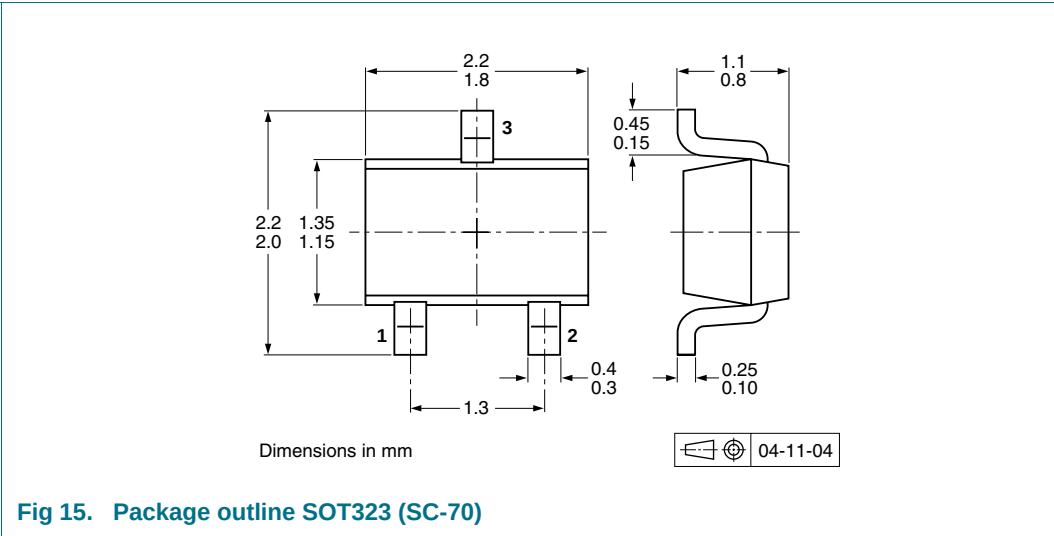


Fig 14. Test circuit for switching times

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PBSS4160U	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering

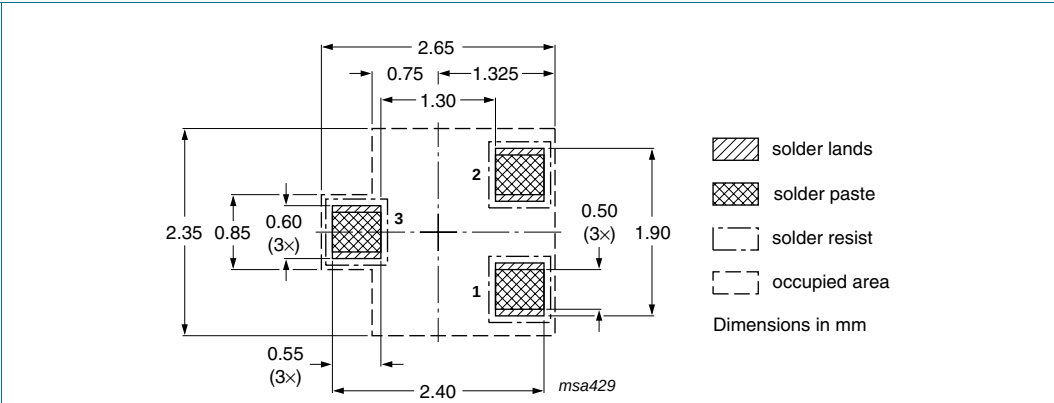


Fig 16. Reflow soldering footprint

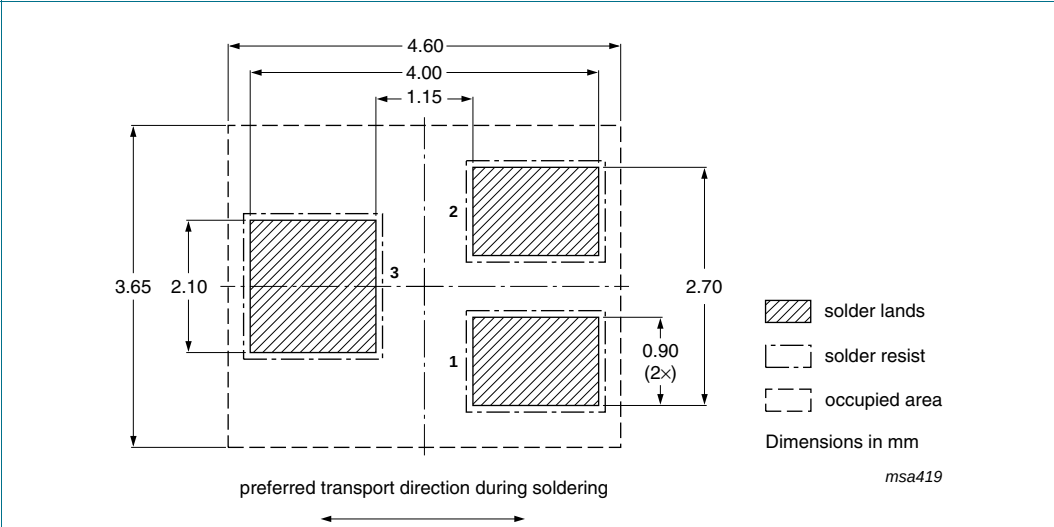


Fig 17. Wave soldering footprint

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160U_3	20091211	Product data sheet	-	PBSS4160U_2
Modifications:	• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. • Figure 16 "Reflow soldering footprint": updated • Figure 17 "Wave soldering footprint": updated			
PBSS4160U_2	20050719	Product data sheet	-	PBSS4160U_1
PBSS4160U_1	20040423	Objective data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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